

~~A1~~  
the component ratio "x" of Al is in a range of  $0.3 \leq x \leq 1.0$ , so that said semiconductor laser light emitting device is configured as an index guide type semiconductor laser light emitting device.

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A2  
9. (Once amended) A semiconductor laser light emitting device comprising:  
a stacked film composed of a stack of group III nitride semiconductor films each containing at least one kind selected from aluminum, gallium, indium, and boron;  
wherein,  
an upper portion of said stacked film is formed into a ridge-like stripe, to form a current injection region;  
a current injection width  $W_{st}$  of said current injection region is in a range of  $1 \mu m \leq W_{st} \leq 3 \mu m$ ;  
a current non-injection region formed on both sides of said ridge-like stripe;  
at least part of said current non-injection region is made from a material expressed by a chemical formula  $Al_xGa_{1-x}N$  ( $0 \leq x \leq 1.0$ ); and  
the component ratio "x" of Al is in a range of  $0.15 < x < 0.30$ , so that said semiconductor laser light emitting device is configured as a weak index type pulsation semiconductor laser light emitting device.

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A3  
17. (Once amended) A semiconductor laser light emitting device comprising:  
a stacked film composed of a stack of group III nitride semiconductor films each containing at least one kind selected from aluminum, gallium, indium, and boron;